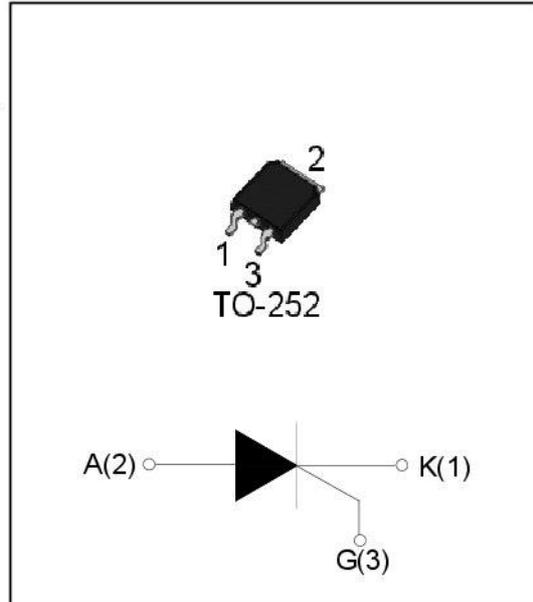




DESCRIPTION: 2P4M TO-252

The 2P4M SCR series provide high dv/dt rate with strong resistance to electromagnetic interface. They are especially recommended for use on residual current circuit breaker, straight hair, igniter etc.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	2	A
I_{GT}	≤ 60	μA
V_{DRM}/ V_{RRM}	600	V

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit	
Storage junction temperature range	T_{stg}	-40-150	$^{\circ}C$	
Operating junction temperature range	T_j	-40-110	$^{\circ}C$	
Repetitive peak off-state voltage	V_{DRM}	600	V	
Repetitive peak reverse voltage	V_{RRM}	600	V	
RMS on-state current	$I_{T(RMS)}$	TO-92 ($T_c=63^{\circ}C$)	2	A
		SOT-89 ($T_c=75^{\circ}C$)		
		TO-126/SOT-223 ($T_c=80^{\circ}C$)		
		TO-252 TO-251 ($T_c=90^{\circ}C$)		
Non repetitive surge peak on-state current (tp=10ms)	I_{TSM}	20	A	
I^2t value for fusing (tp=10ms)	I^2t	2	A^2s	
Critical rate of rise of on-state current	dI/dt	50	$A/\mu s$	
Peak gate current (tp=20 μs , $T_j=110^{\circ}C$)	I_{GM}	0.2	A	

Peak gate power (tp=20μs, Tj=110°C)	P _{GM}	0.5	W
Average gate power dissipation(Tj=110°C)	P _{G(AV)}	0.1	W

ELECTRICAL CHARACTERISTICS (Tj=25°C unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I _{GT}	V _D =12V R _L =33Ω	-	30	60	μA
V _{GT}		-	0.6	0.8	V
V _{GD}	V _D =V _{DRM} Tj=110°C	0.2	-	-	V
I _L	I _G =1.2 I _{GT}	-	-	6	mA
I _H	I _T =0.05A	-	-	5	mA
dV/dt	V _D =2/3V _{DRM} Tj=110°C R _{GK} =1KΩ	20	-	-	V/μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V _{TM}	I _T =4A tp=380μs	Tj=25°C	1.5	V
I _{DRM}	V _D =V _{DRM} V _R =V _{RRM}	Tj=25°C	5	μA
I _{RRM}		Tj=110°C	100	μA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R _{th(j-c)}	junction to case	TO-92	10	°C/W
		TO-126	7.0	
		SOT-89	8.3	
		TO-251 TO-252	6.5	
		SOT-223	7.3	

